

**IN THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

1-9.(Canceled)

10.(Currently Amended) A semiconductor device having a pixel TFT provided in a display region and a driver circuit TFT provided ~~around said display region~~ in a driver circuit, both TFTs formed over a same substrate, said semiconductor device comprising:

said pixel TFT comprising at least one lightly doped region disposed so as not to overlap ~~[[said]]~~ a gate electrode of said pixel TFT;

first n-channel TFT of said driver circuit comprising at least one lightly doped region disposed so as to overlap ~~[[said]]~~ a gate electrode of said first n-channel TFT; and

second n-channel TFT of said driver circuit comprising at least one lightly doped region disposed so that at least a portion thereof overlaps ~~[[said]]~~ a gate electrode of said second n-channel TFT; ~~and,~~

wherein said gate electrodes of said pixel TFT and said driver circuit TFT ~~formed from~~ comprises a first conductive layer,

wherein said gate electrodes are in electrical contact with gate wirings ~~formed from~~ comprising a second conductive layer ~~through connectors provided in areas~~ outside channel-forming regions of said pixel TFT and said driver circuit TFT.

11 (Original). A semiconductor device according to claim 10, wherein a storage capacitor is formed in said display region by a semiconductor layer connected to a source or a drain region of said pixel TFT and contains a single conductive impurity element, a capacitor wiring and an insulating film between said semiconductor layer and said capacitor wiring, and wherein said capacitor wiring is formed by said first conductive layer and said second conductive layer.

12 (Previously presented). A semiconductor device according to claim 10, wherein said first conductive layer comprises at least one selected from Ta, W, Ti and Mo, and said second conductive layer comprises of Al or Cu.

13 (Previously presented). A semiconductor device according to claim 10, wherein said first conductive layer comprises a conductive layer (A) containing nitrogen and at least one selected from Ta, W, Ti and Mo, a conductive layer (B) formed on said conductive layer (A) and comprising at least one selected from Ta, W, Ti and Mo, and a conductive layer (C) formed on regions where said conductive layer (B) does not contact said conductive layer (A) and containing nitrogen and at least one selected from Ta, W, Ti and Mo, and

wherein said second conductive layer comprises a conductive layer (D) comprising Al or Cu and a conductive layer (E) comprising at least one selected from Ta, W, Ti and Mo.

14 (Original). A semiconductor device according to claim 13, wherein said conductive layer (B) contains argon as an added element, and an oxygen concentration in said conductive layer (B) is 30 ppm or less.

15 (Previously presented). A semiconductor device according to claim 10, wherein said first conductive layer comprises a conductive layer (A) containing nitrogen and at least one selected from Ta, W, Ti and Mo, a conductive layer (B) formed on said conductive layer (A) and comprising at least one selected from Ta, W, Ti and Mo and a conductive layer (C) formed on regions where said conductive layer (B) does not contact said conductive layer (A) and containing nitrogen and at least one selected from Ta, W, Ti and Mo, and

wherein said second conductive layer comprises a conductive layer (D) comprising Al or Cu and a conductive layer (E) comprising at least one selected from Ta, W, Ti and Mo, and

wherein said conductive layer (C) and said conductive layer (D) are in contact at said connectors.

16 (Original). A semiconductor device according to claim 15, wherein said conductive layer (B) contains argon as an added element, and an oxygen concentration in said conductive layer (B) is 30 ppm or less.

17 (Original). A semiconductor device according to claim 10, wherein said semiconductor device is an EL display device.

18 (Original). A semiconductor device according to claim 10, wherein said semiconductor device is one selected from the group consisting of a personal computer, a video camera, a portable information terminal, a digital camera and a digital video disk player.

19.(Currently Amended) A semiconductor device having a display region and a driver circuit provided ~~around said display region~~ over a same substrate, said semiconductor device comprising:

said display region comprising a pixel TFT provided with a lightly doped region not overlapping a gate electrode of said pixel TFT; and

said driver circuit comprising at least a first n-channel TFT provided with a whole lightly doped region overlapping a gate electrode of said first n-channel TFT and a second n-channel TFT provided with a portion of a lightly doped region overlapping a gate electrode of said second n-channel TFT,

wherein at least said gate electrodes of said pixel TFTs and said first and second n-channel TFTs ~~are formed from~~ comprises a first conductive layer, and gate wirings connected to said gate electrodes ~~are formed from~~ comprising a second conductive layer, and

wherein said gate electrodes and said gate wirings are electrically connected ~~through connectors~~ in areas outside channel-forming regions of said pixel TFT and said driver circuit TFT.

20 (Original). A semiconductor device according to claim 19, wherein a storage capacitor is formed in said display region by a semiconductor layer connected to a source or a drain region of said pixel TFT and contains a single conductive impurity element, a capacitor wiring and an insulating film between said semiconductor layer and said capacitor wiring, and wherein said capacitor wiring is formed by said first conductive layer and said second conductive layer.

21 (Previously presented). A semiconductor device according to claim 19, wherein said first conductive layer comprises at least one selected from Ta, W, Ti and Mo, and said second conductive layer comprises Al or Cu.

22 (Previously presented). A semiconductor device according to claim 19, wherein said first conductive layer comprises a conductive layer (A) containing nitrogen and at least one selected from Ta, W, Ti and Mo, a conductive layer (B) formed on said conductive layer (A) and comprising at least one selected from Ta, W, Ti and Mo, and a conductive layer (C) formed on regions where said conductive layer (B) does not contact said conductive layer (A) and containing nitrogen and at least one selected from Ta, W, Ti and Mo, and

wherein said second conductive layer comprises a conductive layer (D) comprising Al or Cu and a conductive layer (E) comprising at least one selected from Ta, W, Ti and Mo.

23 (Original). A semiconductor device according to claim 22, wherein said conductive layer (B) contains argon as an added element, and an oxygen concentration in said conductive layer (B) is 30 ppm or less.

24 (Previously presented). A semiconductor device according to claim 19, wherein said first conductive layer comprises a conductive layer (A) containing nitrogen and at least one selected from Ta, W, Ti and Mo, a conductive layer (B) formed on said conductive layer (A) and comprising at least one selected from Ta, W, Ti and Mo and a conductive layer (C) formed on regions where said conductive layer (B) does not contact said conductive layer (A) and containing nitrogen and at least one selected from Ta, W, Ti and Mo,

wherein said second conductive layer comprises a conductive layer (D) comprising Al or Cu and a conductive layer (E) comprising at least one selected from Ta, W, Ti and Mo, and

wherein said conductive layer (C) and said conductive layer (D) are in contact at said connectors.

25 (Original). A semiconductor device according to claim 24, wherein said conductive layer (B) contains argon as an added element, and an oxygen concentration in said conductive layer (B) is 30 ppm or less.

26 (Original). A semiconductor device according to claim 19, wherein said semiconductor device is an EL display device.

27 (Original). A semiconductor device according to claim 19, wherein said semiconductor device is one selected from the group consisting of a personal computer, a video camera, a portable information terminal, a digital camera and a digital video disk player.

28-67.(Canceled)

68 (Previously presented). A semiconductor device comprising:

a semiconductor layer over a substrate, said semiconductor layer comprising a pair of impurity regions and a channel region interposed therebetween;

a gate electrode over said channel region with a gate insulating film interposed therebetween, said gate electrode comprising a first conductive layer; and

a gate wiring in contact with said gate electrode, said gate wiring comprising a second conductive layer which is a different material from said first conductive layer,

wherein said gate wiring is provided outside said channel region.

69 (Previously presented). A semiconductor device according to claim 68, wherein said first conductive layer comprises at least one selected from Ta, W, Ti and Mo, and said second conductive layer comprises Al or Cu.

70 (Previously presented). A semiconductor device according to claim 68, wherein said semiconductor device is an EL display device.

71 (Previously presented). A semiconductor device according to claim 68, wherein said semiconductor device is one selected from the group consisting of a personal computer, a video camera, a portable information terminal, a digital camera and a digital video disk player.

72-75.(Canceled)

76 (Previously presented). A semiconductor device comprising:

a semiconductor layer over a substrate, said semiconductor layer comprising a pair of impurity regions and a channel region interposed therebetween;

a gate electrode over said channel region with a gate insulating film interposed therebetween, said gate electrode comprising a first conductive layer; and

a gate wiring overlapping said gate electrode, said gate wiring comprising a second conductive layer which is a different material from said first conductive layer,

wherein said gate wiring is provided outside said channel region.

77 (Previously presented). A semiconductor device according to claim 76, wherein said first conductive layer comprises at least one selected from Ta, W, Ti and Mo, and said second conductive layer comprises Al or Cu.

78 (Previously presented). A semiconductor device according to claim 76, wherein said semiconductor device is an EL display device.

79 (Previously presented). A semiconductor device according to claim 76, wherein said semiconductor device is one selected from the group consisting of a personal computer, a video camera, a portable information terminal, a digital camera and a digital video disk player.

80.(New) A semiconductor device comprising:

a semiconductor layer over a substrate, said semiconductor layer comprising a pair of impurity regions and a channel region interposed therebetween;

a gate electrode over said channel region with a gate insulating film interposed therebetween, said gate electrode comprising a first conductive layer; and

a gate wiring in contact with said gate electrode, said gate wiring comprising a second conductive layer, wherein said gate wiring is provided outside said channel region;



a storage capacitor comprising a portion of said semiconductor layer, a portion of said gate insulating film, a same material as said first conductive layer, and a same material as said second conductive layer.

81.(New) A semiconductor device according to claim 80, wherein said first conductive layer comprises at least one selected from Ta, W, Ti and Mo, and said second conductive layer comprises Al or Cu.

82.(New) A semiconductor device according to claim 80, wherein said semiconductor device is an EL display device.

83.(New) A semiconductor device according to claim 80, wherein said semiconductor device is one selected from the group consisting of a personal computer, a video camera, a portable information terminal, a digital camera and a digital video disk player.